

Description

The AO4435 is the high cell density trench P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The AO4435 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

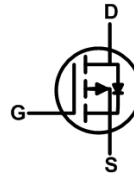
Features

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

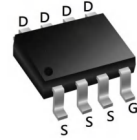
V_{DSS} -30 V
 I_D -10 A
 $R_{DS(ON)}$ 16m Ω

GK xxx
4435

LOGO GK xxx CODE



Schematic Diagram



SOP-8 top & bottom view

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	-10
		$T_C = 100^\circ\text{C}$	-7
I_{DM}	Pulsed Drain Current ^{note1}	-40	A
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	3.7
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	33.8	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.5	-2.4	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} = -10V, I _D = -10A	-	16	23	mΩ
		V _{GS} = -4.5V, I _D = -5A	-	25	34	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	-	1550	-	pF
C _{oss}	Output Capacitance		-	327	-	pF
C _{rss}	Reverse Transfer Capacitance		-	278	-	pF
Q _g	Total Gate Charge	V _{DS} = -15V, I _D = -9.1A, V _{GS} = -10V	-	30	-	nC
Q _{gs}	Gate-Source Charge		-	5.3	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	7.6	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -6A, V _{GS} =-10V, R _{GEN} =2.5Ω	-	14	-	ns
t _r	Turn-on Rise Time		-	20	-	ns
t _{d(off)}	Turn-off Delay Time		-	95	-	ns
t _f	Turn-off Fall Time		-	65	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-10	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-40	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -10A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

RATING AND CHARACTERISTIC CURVES

Figure 1: Output Characteristics

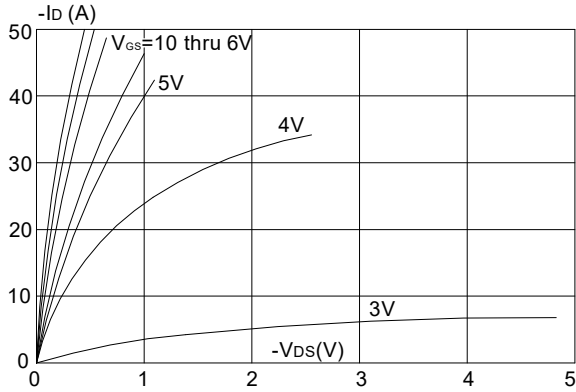


Figure 2: Typical Transfer Characteristics

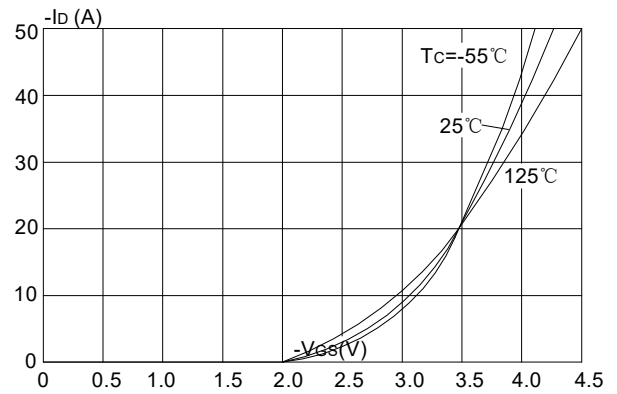


Figure 3: On-resistance vs. Drain Current

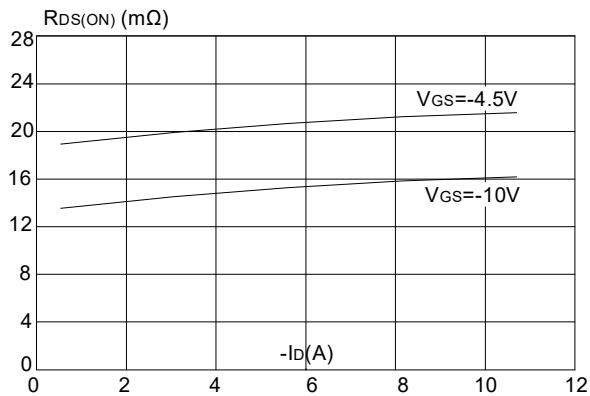


Figure 4: Body Diode Characteristics

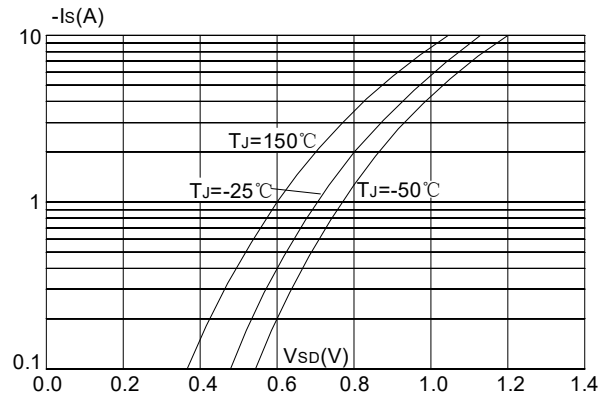


Figure 5: Gate Charge Characteristics

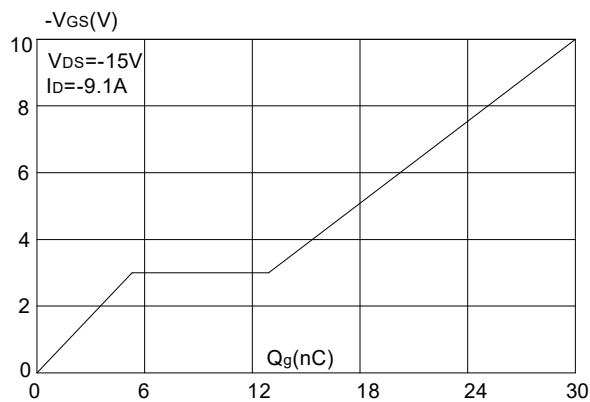
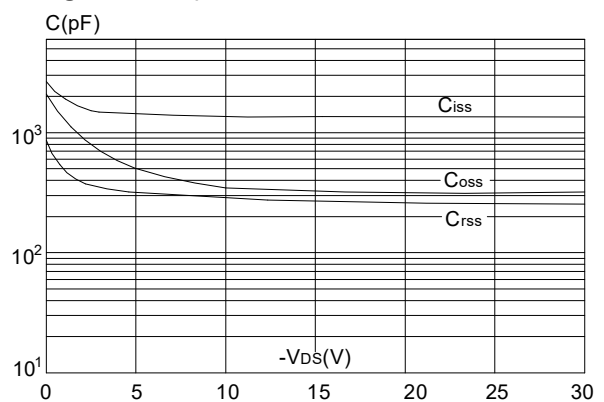


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

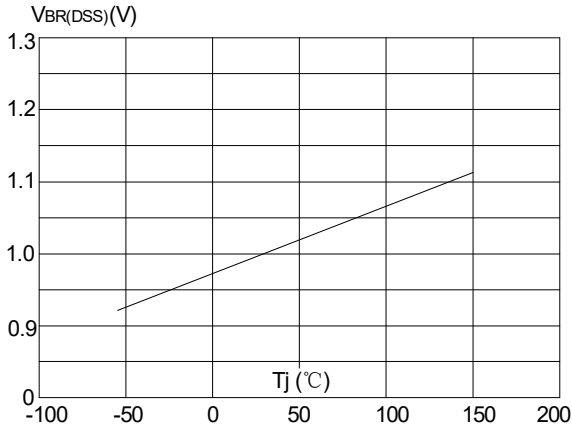


Figure 8: Normalized on Resistance vs. Junction Temperature

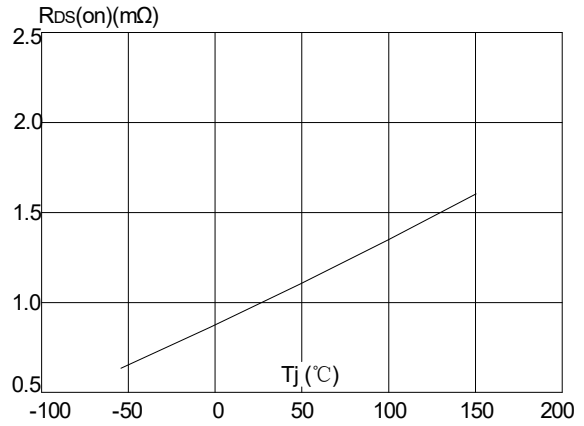


Figure 9: Maximum Safe Operating Area

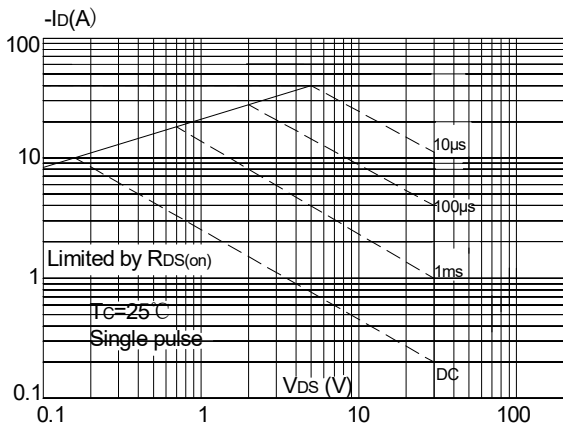


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

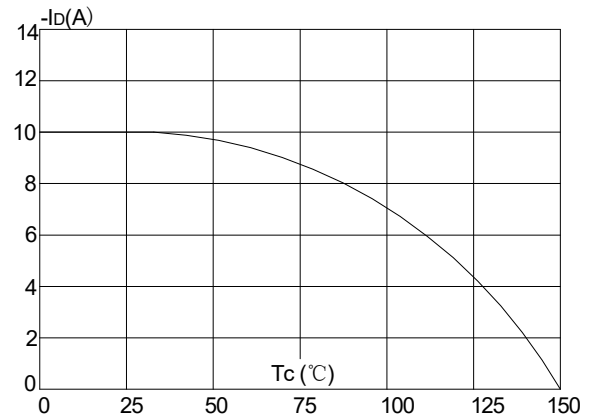
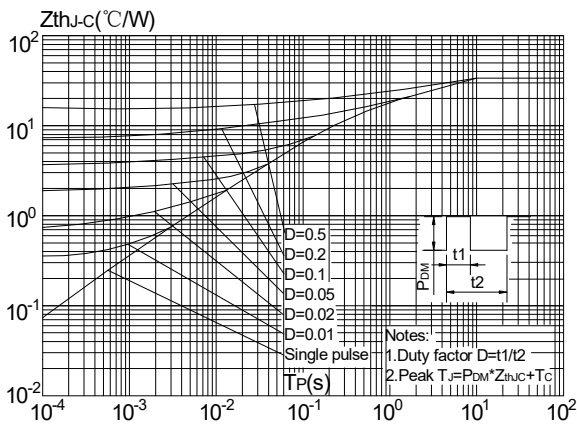


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



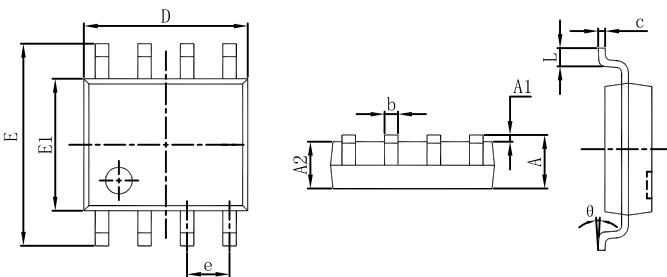
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C

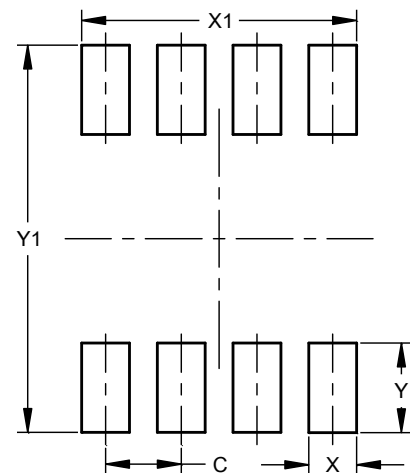


Package Dimensions & Suggested Pad Layout

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Dimensions	Value (in mm)
C	1.27
X	0.70
X1	4.51
Y	2.00
Y1	7.00

Tape & reel specification

Tape		Symbol	Dimension (mm)
		P0	4.00±0.20
		P1	8.00±0.20
		P2	2.00±0.20
		D0	1.55±0.20
		D1	1.55±0.20
		E	1.75±0.15
		F	5.50±0.20
		W	12.00±0.20
		A0	7.00±0.20
		B0	5.70±0.20
		K0	1.35±0.20
		T	0.23±0.20
		13" Reel	
		D3	73Min.
		D4	13.5±2.5
		W1	16.0±3.0
		Quantity: 3000PCS	
13" Reel		D2	330.0±5.0
		D3	73Min.
		D4	13.5±2.5
		W1	16.0±3.0
		Quantity: 4000PCS	